

CS ~~E~~
wherein the step of forming the conductive pattern comprises the step of forming a conductive pattern in the closed via, in the open via and on the dielectric layer opposite the substrate.

Please add the following new claims 40 and 41:

CS ~~40~~
40. (New) A method of forming bonding pad for an integrated circuit comprising the steps of:
forming a dielectric layer on an integrated circuit substrate, the dielectric layer including a closed via therein that encloses an inner portion of the dielectric layer, and is enclosed by an outer portion of the dielectric layer, wherein the closed via penetrates the dielectric layer and extends towards the integrated circuit substrate; and
forming a conductive pattern in the closed via and on the dielectric layer opposite the substrate.

~~41~~
41. (New) A method according to Claim 40 wherein the step of forming the conductive pattern comprises forming the conductive pattern in the closed via and on the dielectric layer opposite the substrate, wherein the conductive pattern penetrates the dielectric layer and extends towards the integrated circuit substrate.